Kinetically Determined Bond Dissociation Energies in Hexamethyldisilane

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Summary A re-investigation of the thermolysis of hexamethyldisilane gives $D(\text{Me}_3\text{Si}-\text{SiMe}_3)$ as 337 kJ mol^{-1} (80.5 kcal mol⁻¹), the Arrhenius A factor for this dissociation being $10^{17.53}\text{s}^{-1}$; $D(\text{Me}_3\text{Si}-\text{H})$ is estimated as 368 kJ mol^{-1} . therefore re-investigated this thermolysis in a stirred-flow system between 770 K and 872 K, with low concentrations of hexamethyldisilane $(4\cdot3 \times 10^{-9} \text{ to } 3\cdot6 \times 10^{-7} \text{ mol cm}^{-3})$ in a nitrogen stream above atmospheric pressure, excess of *m*-xylene being present in some runs.

With no xylene present, the main product was trimethylsilane, with smaller amounts of tetramethylsilane, the isomer of hexamethyldisilane⁴ [Me₃SiCH₂Si(H)Me₂], and 1,1,3,3-tetramethyl-1,3-disilacyclobutane. With added xylene, trimethylsilane and the isomer of hexamethyldisilane were formed at reduced rates, while the formation of the disilacyclobutane was suppressed. First-order rate con-

THE thermolysis of hexamethyldisilane at low pressure has been interpreted in terms of a radical non-chain sequence, to give Arrhenius parameters for the rupture of the siliconsilicon bond,¹ but the A factor thus obtained is unreasonably low in relation to recent values^{2,3} of the rate constant for recombination of trimethylsilyl radicals. We have

stants for the formation of trimethylsilane in xylene were given by $k/s^{-1} = 10^{17 \cdot 53 \pm 0.25} \exp(-336.6 \pm 4.0/RT)$ (activation energy in kJ mol⁻¹). The following sequence of reactions accounts for the thermolysis of hexamethyldisilane in *m*-xylene (RH).

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$$Me_sSiSiMe_s \rightarrow 2Me_sSi$$
 (1)

$$Me_{a}Si + RH \rightarrow Me_{a}SiH + R \cdot$$
 (2)

$$R_{\bullet} + Me_{3}SiSiMe_{3} \rightleftharpoons RH + Me_{5}Si_{2}CH_{2}$$
 (3), (-3)

$$Me_{5}Si_{2}CH_{2} \rightarrow Me_{3}SiCH_{2}SiMe_{2}$$
 (4)

$$Me_3SiCH_2SiMe_2 + RH \rightarrow Me_3SiCH_2Si(H)Me_2 + R.$$
 (5)

$$2 \mathbf{R} \cdot \longrightarrow \mathbf{R}_2 \tag{6}$$

It appears that the added xylene inhibits a chain reaction which produces all of the disilacyclobutane and the extra trimethylsilane formed in the absence of xylene, the chain propagating step being

$$Me_3SiCH_2SiMe_2 \rightarrow Me_3Si \cdot + CH_2:SiMe_2$$
 (7)

In xylene, reaction (7) cannot compete with reaction (5).

Hence, the thermolysis of hexamethyldisilane at low pressure is not a non-chain process, as was previously

 $\dagger 1$ Thermochemical calorie = $4 \cdot 184$ J.

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- ⁷ R. Walsh, reported at Gas Kinetics Discussion Group Meeting, Leicester, 1972.

believed,^{1,5} but proceeds by a chain of short length (be-
tween 4.5 and 2.1 under the above conditions). Con-
sequently the Arrhenius parameters for the formation of
trimethylsilane in the presence of excess of xylene are the
best available measure of
$$k_1$$
. The A factor of $10^{17.53}$ s⁻¹ is
now satisfactorily consistent with that³ for reaction (-1),
and while a value of 337 kJ mol⁻¹ (80.5 kcal mol⁻¹)[†] for
 $D(Me_3Si-SiMe_3)$ represents a substantial increase on the
previously accepted value⁵ there is other evidence in support
of it; recent electron impact experiments⁶ give $D(Me_3Si-H)$
 $-D(Me_3Si-SiMe_3) = 31 \text{ kJ mol}^{-1}$ whence $D(Me_3Si-H) = 368 \text{ kJ mol}^{-1}$ (88 kcal mol⁻¹), in good agreement with the value
of approximately 372 kJ mol⁻¹ (89 kcal mol}^{-1}) obtained by
Walsh from experiments on the rate of iodination of tri-
methylsilane.⁷

The tetramethylsilane may be formed by direct silvlene elimination

$$Me_3Si-SiMe_3 \rightarrow Me_4Si + Me_2Si$$
 (8)

and the earlier Arrhenius parameters1 probably related to this process rather than to the rupture of the silicon-silicon bond.

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